

SCDS346A - JUNE 2013 - REVISED JULY 2013

# Autonomous Audio Headset Switch with Reduced GND Switch R<sub>ON</sub> and FM Capability

Check for Samples: TS3A226AE

#### FEATURES

- Ground FET Switches (60mΩ typical)
- Autonomous Detection of Headset Types: 3-Poles or 4-Poles (with MIC on SLEEVE or RING2)
- Microphone Line Switches
- Supports FM Signal Transmission Through the Ground FETs
- Reduction of Click/Pop Noise
- VDD Range: 2.6 V 4.7 V
- THD (Mic): 0.002% Typical
- Low Current Consumption: 6.5-µA Typical
- ±8kV Contract Discharge (IEC 61000-4-2) ESD Performance on SLEEVE and RING2 Pins

#### **APPLICATIONS**

- Mobile Phones / Tablet PCs
- Notebook/Ultrabook Computers

### DESCRIPTION

The TS3A226AE is an audio headset switch that detects 3- or 4-pole 3.5mm accessories. For a 4-pole accessory with a microphone, the TS3A226AE also detects the MIC location and routes the microphone and ground signals automatically. The ground signal is routed through a pair of low-impedance ground FETs ( $60m\Omega$  typical), resulting minimal impact on audio cross-talk performance. The autonomous detection feature allows end users to plug in accessories with different audio pole configurations into the mobile device and have them operate properly with no added software control and complexity. The ground FETs of the device are designed to allow FM signal pass-through, making it possible to use the ground line of the headset as an FM antenna in mobile audio application.

The TS3A226AE is packaged within a 1.2mm × 1.2mm WCSP package, making it suitable for use in mobile application.

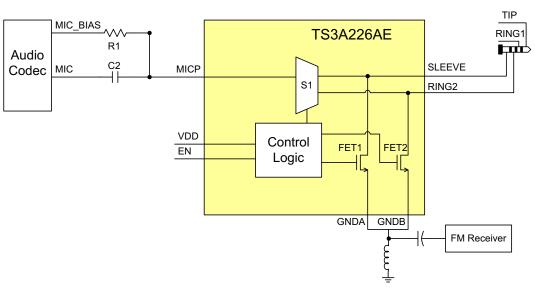


Figure 1. Typical Application Diagram

#### **ORDERING INFORMATION**

For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com

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### TS3A226AE

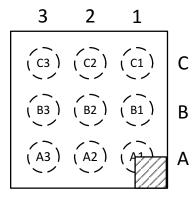
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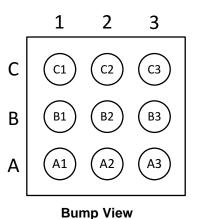




These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### PACKAGE; YFF-WCSP





**Top View/Footprint** 

Die Size: 1.2mm ×1.2mm Bump Size: 0.25mm

. Bump Pitch: 0.4mm

#### TS3A226AE Pin Mapping (Top View)

	3	2	1
С	GND	TIP	EN
В	SLEEVE	GNDA	MICp
Α	RING2	GNDB	VDD

#### **PIN FUNCTIONS**

PIN			
NUMB ER	NAME	TYPE	DESCRIPTION
A1	VDD	Supply	Power supply for the chip.
A2	GNDB	Ground	FET2 ground reference.
A3	RING2	I/O	Connected to the RING2 segment of the jack. The pin will be routed automatically by TS3A226AE to either MICp or GNDB depending on the type of accessory.
B1	MICp	I/O	Microphone signal connection to codec. Microphone bias should be fed into this pin.
B2	GNDA	Ground	FET1 ground reference.
B3	SLEEVE	I/O	Connected to the SLEEVE segment of the jack. The pin will be routed automatically by TS3A226AE to either MICp or GNDA depending on the type of accessory.
C1	EN	Input	A rising edge triggers the detection sequence. This pin can be connected to the headset jack to allow automatic pull-up to supply after headset insertion.
C2	TIP	I/O	Connected to the TIP segment of the headphone jack.
C3	GND	Ground	Chip ground reference.



#### S1 MUX DETAIL

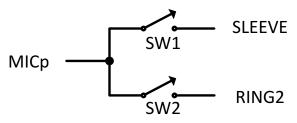


Figure 2. S1 Mux Detail

#### FUNCTIONAL TABLES: INTERNAL SWITCHES

EN	Accessory Type	Accessory Configuration	SW1	SW2	FET1	FET2
0	N/A	—	High Z	High Z	High Z	High Z
1	TRS 3-pole Headphone or Speaker	TIP = Audio Left Ring = Audio Right Sleeve = <b>Ground</b>	On	On	On	On
1	TRRS 4-pole Headphone	TIP = Audio Left Ring1 = Audio Right Ring2 = <b>Ground</b> Sleeve = <b>Microphone</b>	On	High Z	High Z	On
1	TRRS 4-pole Headphone	TIP = Audio Left Ring1 = Audio Right Ring2 = <b>Microphone</b> Sleeve = <b>Ground</b>	High Z	On	On	High Z
1	N/A		On	On	On	On

#### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		VALUE	UNIT
V	Voltage range on VDD <sup>(2)</sup>	-0.3 to 5	V
VI	Voltage range on EN, MICP, RING2, SLEEVE, TIP <sup>(2)</sup>	–0.3 to V <sub>DD</sub> +0.5	V
T <sub>A</sub>	Operating ambient temperature range <sup>(3)</sup>	-40 to 85	°C
T <sub>J (MAX)</sub>	Maximum operating junction temperature	125	°C
T <sub>stg</sub>	Storage temperature range	-65 to 150	°C
	Charge device model (JESD 22 C101)	500	V
ESD rating	Human body model(JESD 22 A114)	2	kV
	Contact discharge on RING2, SLEEVE, TIP (IEC 61000-4-2)	8	kV

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to network ground terminal.

(3) In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature may have to be derated. Maximum ambient temperature  $[T_{A(max)}]$  is dependent on the maximum operating junction temperature  $[T_{J(max)}]$ , the maximum power dissipation of the device in the application  $[P_{D(max)}]$ , and the junction-to-ambient thermal resistance of the part/package in the application ( $\theta_{JA}$ ), as given by the following equation:  $T_{A(max)} = T_{J(max)} - (\theta_{JA} \times P_{D(max)})$ 

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#### **RECOMMENDED OPERATING CONDITIONS**

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V <sub>DD</sub>	Supply voltage range	Supply voltage range			
V <sub>IO</sub>	Input/Output voltage range (E	N, MICP, RING2, SLEEVE, TIP)	0	$V_{DD}$	V
V <sub>IO(TIP)</sub>	Input/Output voltage range for	TIP	-2.0	$V_{DD}$	V
		VDD = 2.6 V	1.16	$V_{DD}$	
VIH	Input Logic High for EN	VDD = 3.3 V	1.24	$V_{DD}$	V
		VDD = 4.5 V	1.48	$V_{DD}$	
		VDD = 2.6 V	0	0.19	
VIL	Input Logic Low for EN	VDD = 3.3 V	0	0.3	V
		VDD = 4.5 V	0	0.5	
T <sub>A</sub>	Operating temperature range		-40	85	°C

#### **KEY ELECTRICAL CHARACTERISTICS**

Unless otherwise noted the specification applies over the V<sub>DD</sub> range and operating junction temperature  $-40^{\circ}C \le T_A \le 70^{\circ}C$ . Typical values are for V<sub>DD</sub> = 3.3V and T<sub>J</sub> = 25°C.

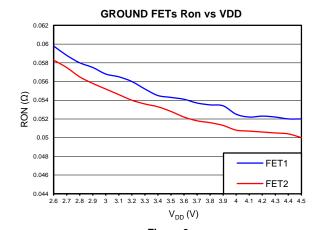
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>DD</sub>	Input Voltage Range		2.6	3.3	4.5	V
I <sub>DD</sub>	Quiescent Current	$V_{DD}$ = 4.5 V, $V_{MICp}$ = 1.8 V to $V_{DD}$ , EN=L or EN=H (after detection)		6.5	14	μA
SWITCH	RESISTANCE					
R <sub>F1</sub>	FET1 On Resistance	V 26V/V 0V/L 10mA		60	85	
R <sub>F2</sub>	FET2 On Resistance	$V_{DD} = 2.6 \text{ V}, V_{GND} = 0 \text{ V}, I_{GND} = 10 \text{ mA}$		60	85	mΩ
R <sub>SW1</sub>	SW1 On Resistance	$V_{DD} = 2.6 \text{ V}, \text{ V}_{\text{SLEEVE/RING2}} = 0 \text{ V} \text{ to } 2.6 \text{ V},$		8.5	10.5	0
R <sub>SW2</sub>	SW2 On Resistance	$I_{MIC} = \pm 10 \text{ mA}$		8.5	10.5	Ω
SWITCH	LEAKAGE CURRENT					
I <sub>OFF-0.1</sub>	FET1 and FET2 off leakage				1	
I <sub>OFF-10</sub>	SW1, SW2 off leakage	$V_{\text{IN}}$ = 0 V to 2.6 V, $V_{\text{OUT}}$ = 0 V, $V_{\text{DD}}$ = 4.5 V			1	μA
I <sub>ON-10</sub>	SW1, SW2 on leakage	_			1	
SWITCH	DYNAMIC CHARACTERISTICS					
BW <sub>F1</sub>	FET1 Bandwidth	V 60 m)/ 1 10 m/	160	200		MHz
BW <sub>F2</sub>	FET2 Bandwidth	$V = 60 \text{ mV}_{PP}, I_{\text{bias}} = 10 \text{ mA}$	160	200		
PSR <sub>217</sub>		V = 200 mV <sub>PP</sub> , f = 217 Hz		-110		dB
PSR <sub>1k</sub>	Power Supply Rejection, $R_1 = 50 \Omega$	$V = 200 \text{ mV}_{PP}, \text{ f} = 1 \text{ kHz}$		-100		dB
PSR <sub>20k</sub>		V = 200 mV <sub>PP</sub> , f = 20 kHz		-85		dB
ISO <sub>S1</sub>	SLEEVE or RING2 to MICP Isolation	V = 200 mV <sub>PP</sub> , f = 20 kHz, R <sub>L</sub> = 50 $\Omega$		-80		dB
SEP <sub>S1</sub>	SLEEVE to RING2 Separation	V = 200 mV <sub>PP</sub> , f = 20 kHz, R <sub>L</sub> = 50 $\Omega$ (see Figure 5)	-80			dB
THD <sub>10</sub>		V = 10 mV <sub>PP</sub> , f = 20-20 kHz, R <sub>S</sub> = 600 Ω		0.01%		
THD <sub>200</sub>	<ul> <li>Total Harmonic Distortion</li> </ul>	V = 200 mV <sub>PP</sub> , f = 20-20 kHz, R <sub>S</sub> = 600 Ω		0.002%		
TIMING	CHARACTERISTICS				Ļ	
t <sub>dect</sub>	Total detection time	From EN=H to S1 switch(es) closing		180		ms



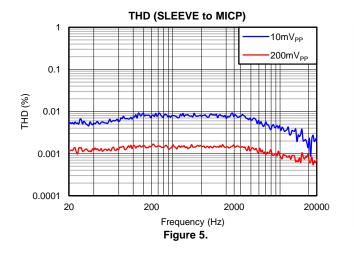
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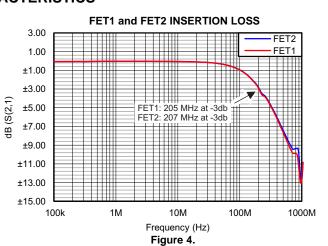
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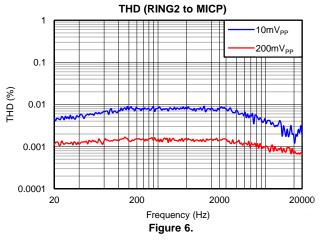
## TYPICAL CHARACTERISTICS











#### **REVISION HISTORY**

Cł	nanges from Original (June 2013) to Revision A P	Page
•	Removed Machine Model ESD specification.	3
•	Added EN=L or EN=H (after detection) to I <sub>DD</sub> TEST CONDITIONS.	4
•	Added typical values to R <sub>SW1</sub> and R <sub>SW2</sub>	4
•	Added t <sub>dect</sub> PARAMETER to KEY ELECTRICAL CHARACTERISTICS table.	4



27-Jul-2013

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
TS3A226AEYFFR	ACTIVE	DSBGA	YFF	9	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	YP2 26AE	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

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Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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# **PACKAGE MATERIALS INFORMATION**

A0 B0 K0 P1 W

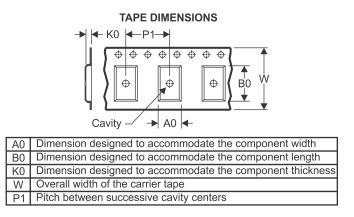
Pin1

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#### **TAPE AND REEL INFORMATION**





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



ł	All dimensions are nominal					
ĺ	Device	Package Type	Package Drawing		Reel Diameter	Reel Width

		Туре	Drawing			Diameter (mm)	Width W1 (mm)	(mm)	(mm)	(mm)	(mm)	(mm)	Quadrant
ſ	TS3A226AEYFFR	DSBGA	YFF	9	3000	180.0	8.4	1.46	1.36	0.7	4.0	8.0	Q1

TEXAS INSTRUMENTS

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## PACKAGE MATERIALS INFORMATION

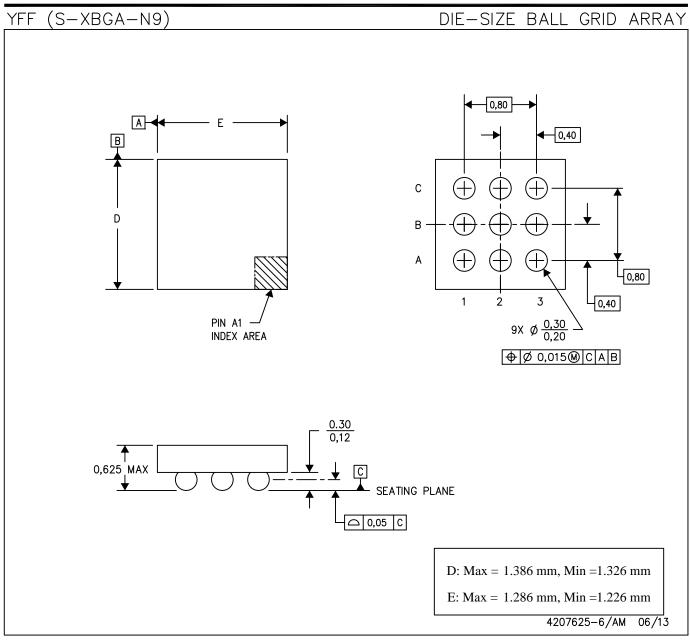
27-Sep-2013



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3A226AEYFFR	DSBGA	YFF	9	3000	182.0	182.0	17.0

## MECHANICAL DATA



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

B. This drawing is subject to change without notice.

C. NanoFree™ package configuration.



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